

Silicon NPN Power Transistors

2SD1263 2SD1263A

DESCRIPTION

- With TO-220Fa package
- High breakdown voltage

APPLICATIONS

- For power amplification

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

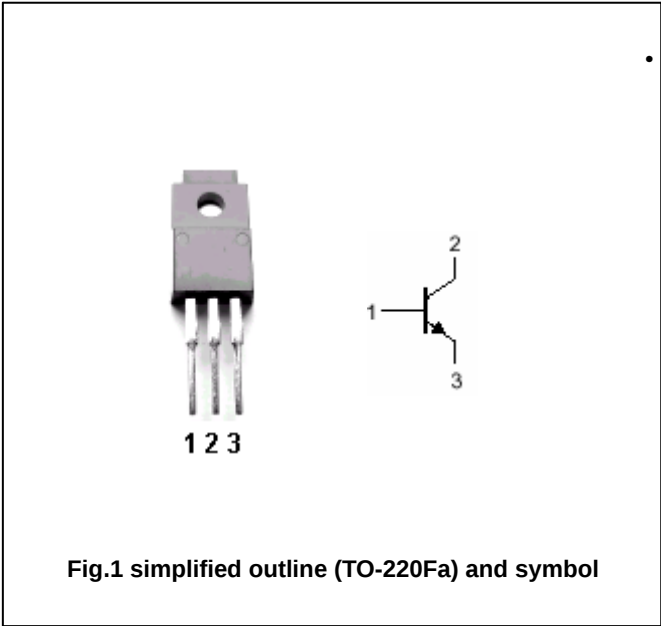


Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SD1263	Open emitter	350	V
		2SD1263A		400	
V _{CEO}	Collector-emitter voltage	2SD1263	Open base	250	V
		2SD1263A		300	
V _{EBO}	Emitter-base voltage		Open collector	5	V
I _C	Collector current			0.75	A
I _{CM}	Collector current-peak			1.5	A
P _C	Collector power dissipation	T _a =25℃		2	W
		T _C =25℃		35	
T _j	Junction temperature			150	℃
T _{stg}	Storage temperature			-55~150	℃

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter voltage	2SD1263	I _C =30mA, I _B =0	250			V
		2SD1263A		300			
V _{CEsat}	Collector-emitter saturation voltage		I _C =1A, I _B =0.2A			1.0	V
V _{BE}	Base-emitter voltage		I _C =1A; V _{CE} =10V			1.5	V
I _{EBO}	Emitter cut-off current		V _{EB} =5V; I _C =0			1.0	mA
I _{CEO}	Collector cut-off current	2SD1263	V _{CE} =150V; I _B =0			1.0	mA
		2SD1263A	V _{CE} =200V; I _B =0			1.0	mA
I _{CES}	Collector cut-off current	2SD1263	V _{CE} =350V; V _{BE} =0			1.0	mA
		2SD1263A	V _{CE} =400V; V _{BE} =0			1.0	mA
h _{FE-1}	DC current gain		I _C =0.3A; V _{CE} =10V	70		250	
h _{FE-2}	DC current gain		I _C =1A; V _{CE} =10V	10			
f _T	Transition frequency		I _C =0.5A; V _{CE} =5V, f=10MHz		30		MHz

Switching times

t _{on}	Turn-on time	I _C =1A; I _{B1} =-I _{B2} =0.1A V _{CC} =50V		0.5		μs
t _s	Storage time			2		μs
t _f	Fall time			0.5		μs

◆ h_{FE-1} Classifications

Q	P
70-150	120-250

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PACKAGE OUTLINE

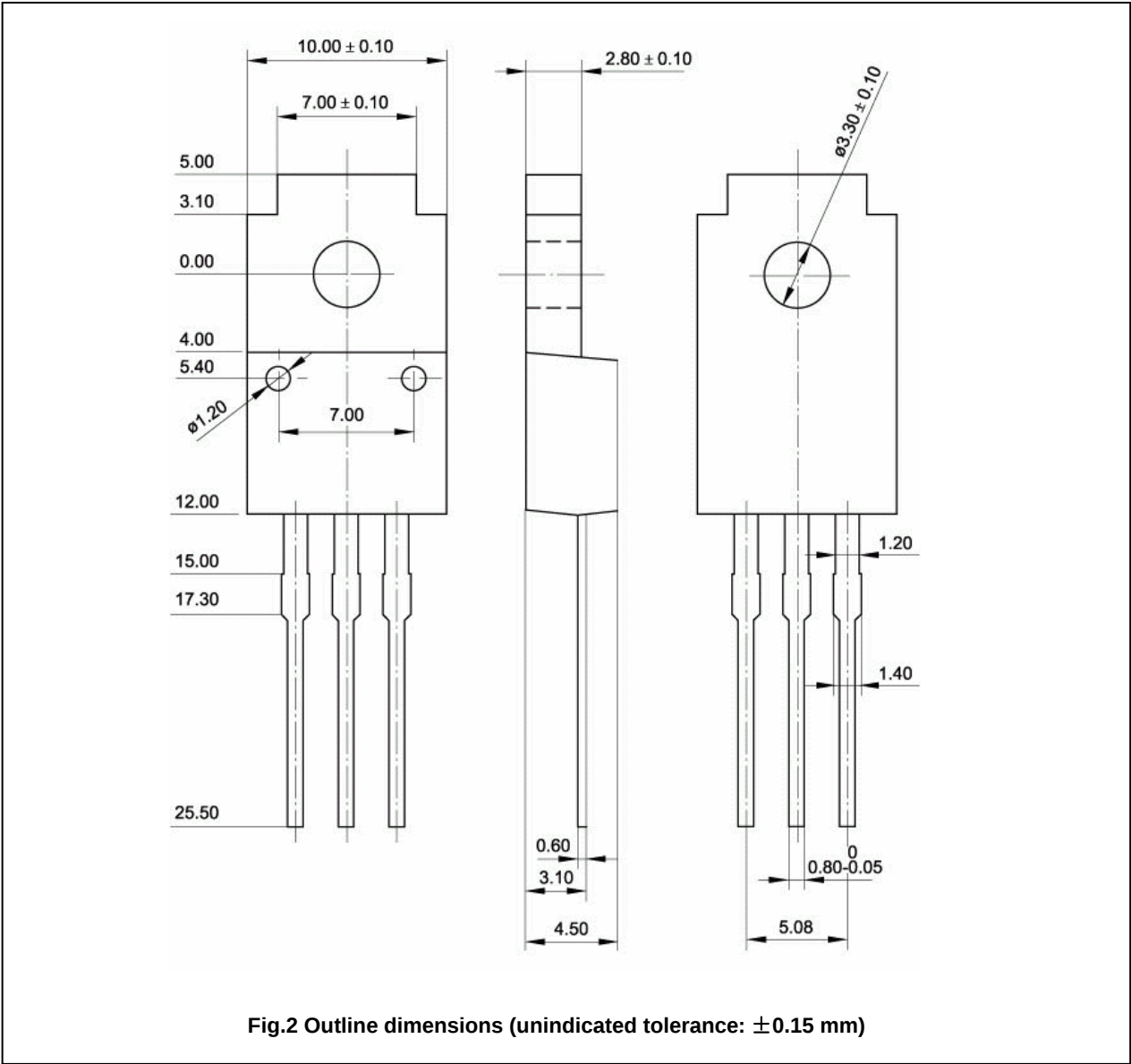


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

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